

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of manufacturing a semiconductor device, comprising:  
mounting a semiconductor chip having electrodes on a substrate having wiring patterns; and  
forming conductive layers on the semiconductor chip that electrically connect the electrodes and the wiring patterns in a manner ~~to pass~~such that the conductive layers are disposed on side surfaces of the semiconductor chip.
2. (Original) The method of manufacturing a semiconductor device according to claim 1, further including face-up bonding the semiconductor chip.
3. (Currently Amended) method of manufacturing a semiconductor device, comprising:  
stacking in layers a plurality of semiconductor chips having electrodes on a substrate having wiring patterns; and  
forming a conductive layer on the semiconductor chip that electrically connects the electrodes of any one of the semiconductor chips and the wiring patterns in a manner ~~to pass~~such that the conductive layer is disposed on a side surface of at least one of the semiconductor chips.
4. (Original) The method of manufacturing a semiconductor device according to claim 3, further including face-up bonding the plurality of semiconductor chips.
5. (Original) The method of manufacturing a semiconductor device according to claim 3, further including mounting a second semiconductor chip, that is smaller than a first semiconductor chip among the plurality of semiconductor chips, on the first semiconductor chip.
6. (Original) The method of manufacturing a semiconductor device according to claim 3, further including forming a second conductive layer that electrically connects the electrodes of one of the semiconductor chips and the electrodes of another of the semiconductor chips in a manner to pass a side surface of at least one of the semiconductor chips.

7. (Original) The method of manufacturing a semiconductor device according to claim 3, further including face-down bonding a first semiconductor chip among the plurality of semiconductor chips to the substrate, and face-up bonding a second semiconductor chip to a side of the first semiconductor chip opposite to a side where the electrodes are formed.

8. (Original) The method of manufacturing a semiconductor device according to claim 1, further including forming the conductive layer by ejecting a solution containing fine-particles of conductive material.

9. (Currently Amended) A semiconductor device, comprising:  
a substrate having wiring patterns;  
a plurality of stacked semiconductor chips having electrodes;  
a conductive layer that is disposed on the semiconductor chip that electrically connects the electrodes of any one of the semiconductor chips and the wiring patterns in a manner such that the conductive layer is disposed on ~~to pass~~ a side surface of at least one of the semiconductor chips; and  
a second conductive layer that electrically connects the electrodes of one of the semiconductor chips and the electrodes of another of the semiconductor chips in a manner to pass a side surface of at least one of the semiconductor chips.

10. (Original) The semiconductor device according to claim 9, the plurality of semiconductor chips being face-up bonded.

11. (Original) The semiconductor device according to claim 10, a second semiconductor chip that is smaller than a first semiconductor chip among the plurality of semiconductor chips being mounted on the first semiconductor chip.

12. (Original) The semiconductor device according to claim 9, a first semiconductor chip among the plurality of semiconductor chips being face-down bonded to the substrate, and a second semiconductor chip being face-up bonded to a side of the first semiconductor chip opposite to a side thereof where the electrodes are formed.

13. (Original) A circuit substrate assembly, comprising:  
a circuit substrate; and  
the semiconductor device according to claim 9 mounted on the circuit substrate.

14. (Original) An electronic equipment, comprising:  
the semiconductor device according to claim 9.